

40 V N-channel Trench MOSFET

2 April 2019

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	40	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	5.4	А
Static chara	octeristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5.4 A; T <sub>j</sub> = 25 °C		-	23	30	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

# nexperia

# 5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G ↓ ↓ ↓ ↓
4	S	source	<b>TSOP6 (SOT457)</b>	
5	D	drain		
6	D	drain	1	
				017aaa255

## 6. Ordering information

### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN30ENEA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMN30ENEA	3Q

### 8. Limiting values

#### Table 5. Limiting values

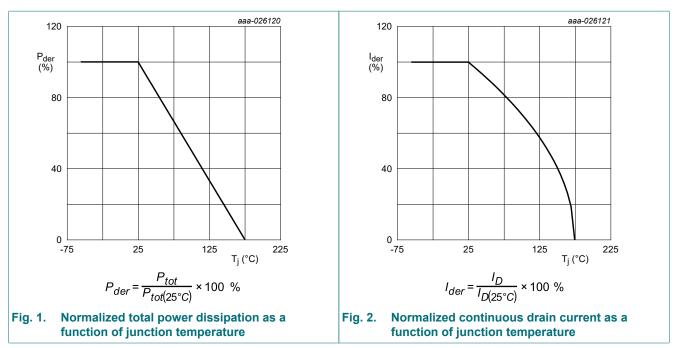
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	5.4	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	3.8	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	22	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	667	mW
			[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.6	А
ESD maximu	m rating				-	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche ru	ggedness			1		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ T_{j(init)} = 25 \text{ °C}; I_D = 0.83 \text{ A}; \text{ DUT in}$ avalanche (unclamped)		-	16.7	mJ

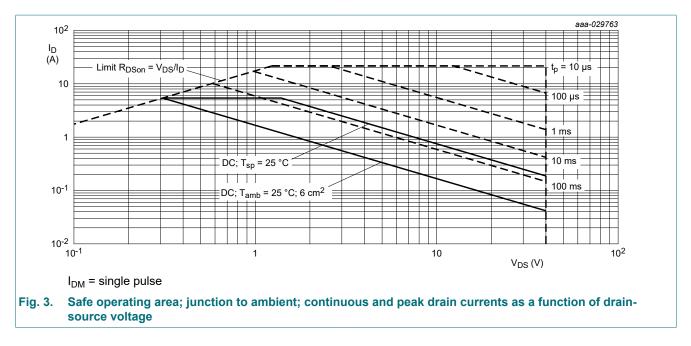
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



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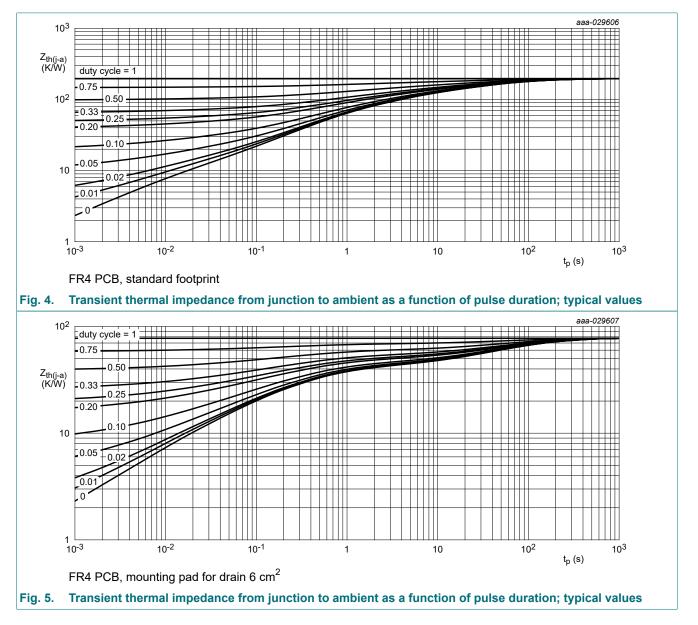


# 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air	[1]	-	195	225	K/W
	junction to ambient		[2]	-	78	90	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

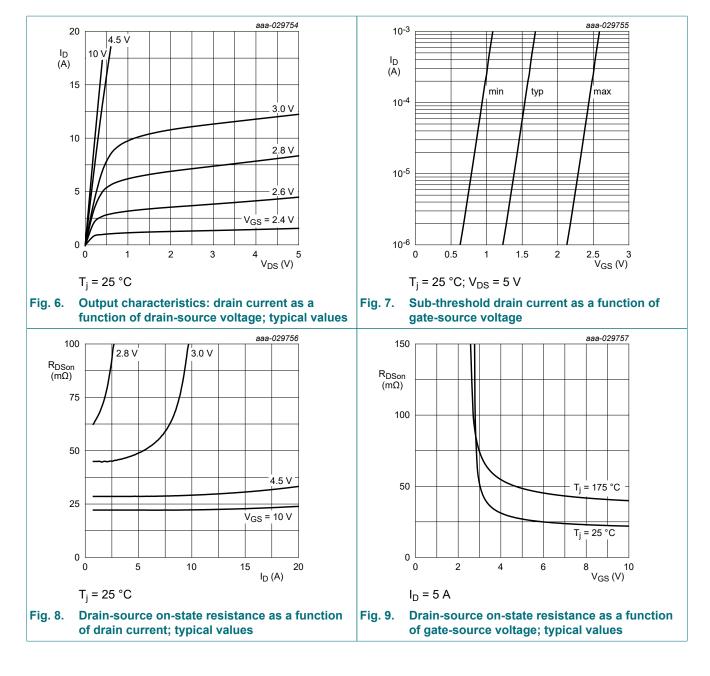
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



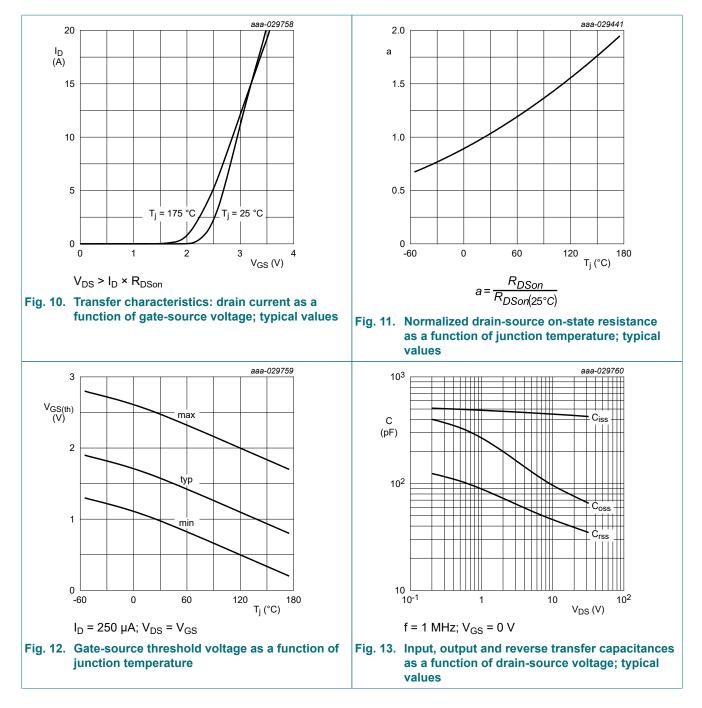
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1	1.6	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
GSS	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5.4 A; T <sub>j</sub> = 25 °C	-	23	30	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5.4 A; T <sub>j</sub> = 175 °C	-	44	57	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 4.7 A; T <sub>i</sub> = 25 °C	-	30	40	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	19	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 10 V;	-	7.8	11.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	440	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	76	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	39	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 10 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	20	-	ns
t <sub>f</sub>	fall time		-	33	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.6 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
trr	reverse recovery time	I <sub>S</sub> = 1.6 A; dI <sub>S</sub> /dt = -100 A/µs;	-	11	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	4	-	nC

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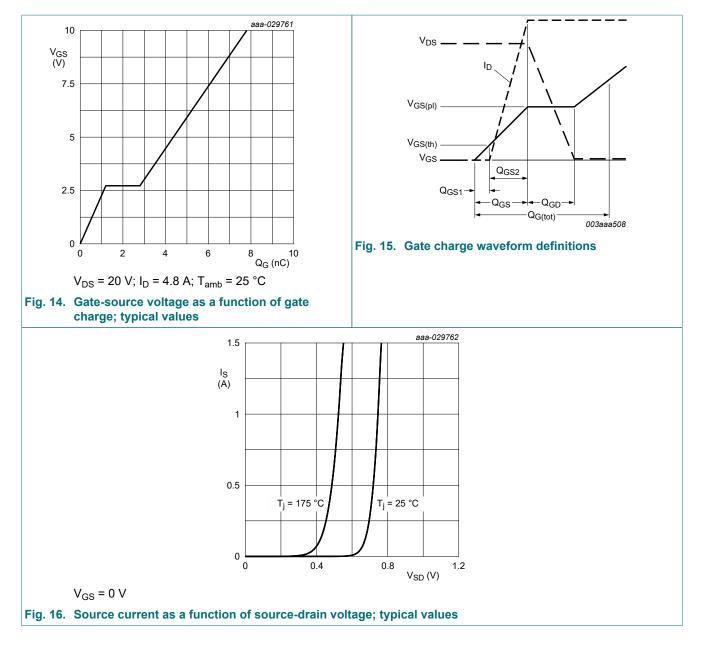


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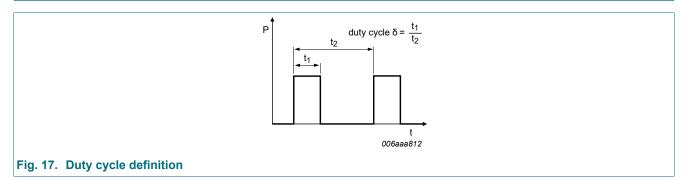
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**Product data sheet** 

### **11. Test information**

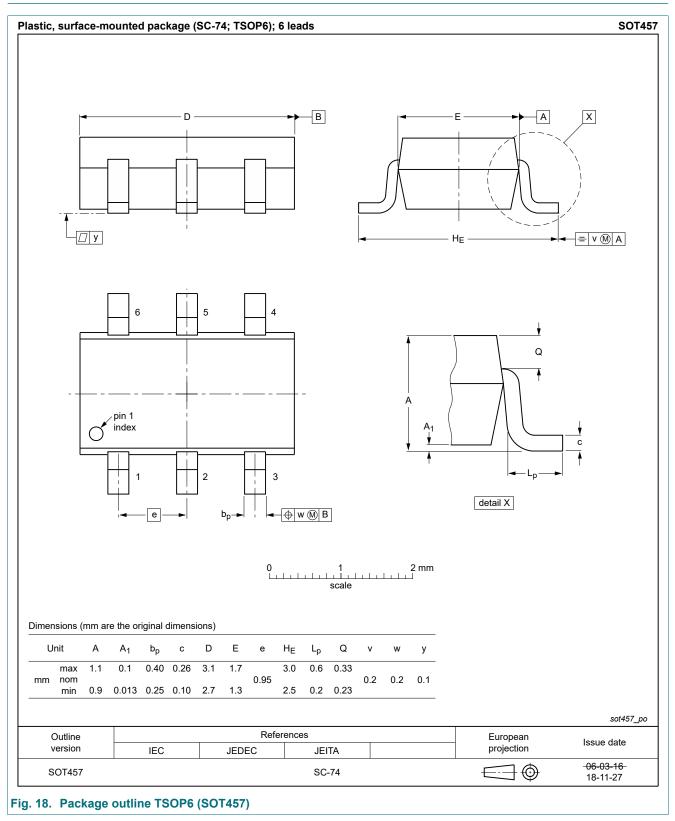


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline



# 13. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMN30ENEA v.1	20190402	Product data sheet	-	-		

## 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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**Product data sheet** 



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